

AN4194 Application note

Flash Programming for SPC560xx, RPC560xx, SPC56APxx, RPC56APxx and SPC563M64xx devices

Introduction

This document describes the operations needed to perform a Flash Programming on SPC560Bxx, RPC560Bxx, SPC560Cxx, SPC560Dxx, SPC560Pxx, SPC56APxx, RPC56APxx and SPC563M64xx Flash.

Supported devices list:

- SPC560D30xx
- SPC560D40xx
- SPC560B40xx
- SPC560B50xx
- SPC560C40xx
- SPC560C50xx
- SPC560B54xx
- SPC560B60xx
- SPC560B64xx
- SPC560P34xx
- SPC560P40xx
- SPC560P44xx
- SPC560P50xx
- SPC560P54xx
- SPC560P60xx
- SPC56AP54xx
- SPC56AP60xx
- SPC563M64xx
- RPC560B64xx

RPC56AP60xx

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1 Flash memory architecture

In the SPC560xx, RPC560xx, SPC56APxx, RPC56APxx and SPC563M64xx families we can find one or more Code Flash blocks and one of the Data Flash blocks (see *Appendix A: Document references*).

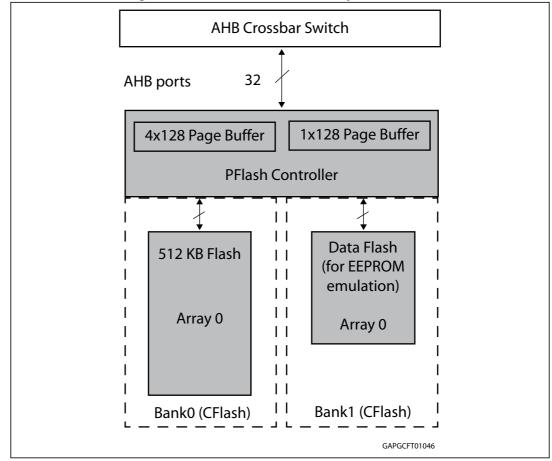


Figure 1. SPC560B50 Flash memory architecture

1.1 Code Flash

The primary function of the Code Flash module is to serve as electrically programmable and erasable non-volatile memory.

1.1.1 Main features

- High read parallelism (128 bits)
- Error correction code (SEC-DED) to enhance Data Retention
- Double word program (64 bits)
- Sector erase
- Single bank
 - Read-While-Write (RWW) not available an individual module
- Erase suspend available (program suspend not available)
- Software programmable program/erase protection to avoid unwanted writings
- Censored mode against piracy
- Shadow sector available
- One-Time Programmable (OTP) area in test Flash block

1.2 Data Flash

The primary function of the Data Flash module is to serve as electrically programmable and erasable non-volatile memory.

1.2.1 Main features

- High read parallelism (128 bits)
- Error correction code (SEC-DED) to enhance data retention
- Double word program (64 bits)
- Sector erase
- Single bank
 - Read-While-Write (RWW) not available
- Erase suspend available (program suspend not available)
- Software programmable program/erase protection to avoid unwanted writings
- Censored mode against piracy
- Not usable as main code memory of the device
- Shadow sector not available
- One-Time Programmable (OTP) area in test Flash block

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2 Programming

As described in the Reference Manual (see *Appendix A: Document references*) to write into the Flash you have to follow several steps while writing in some Flash module registers especially in the Module Configuration Register (MCR)

As described in the Flash chapter of the reference manual, each modify operation is started through a sequence of three steps:

- 1. The first instruction is used to select the desired operation by setting its corresponding selection bit in MCR (PGM or ERS) or UT0 (MRE or EIE).
- 2. The second step is the definition of the operands: the Address and the Data for programming or the Sectors for erase or margin read.
- 3. The third instruction is used to start the modify operation, by setting EHV in MCR or AIE in UT0.

In general each modify operation is completed through a sequence of four steps:

- 1. Wait for operation completion: wait for bit MCR.DONE (or UT0.AID) to go high.
- 2. Check operation result: check bit MCR.PEG (or compare UMISR0-4 with expected value).
- 3. Switch off FPEC by resetting MCR.EHV (or UT0.AIE).
- 4. Deselect current operation by clearing MCR.PGM/ERS (or UT0.MRE/EIE).

2.1 Double word program

The user may program the values in any or all of two words, of a Double Word, with a single program sequence.

Double Word-bound words have addresses which differ only in address bit 2. The Program operation consists of the following sequence of events:

- Change the value in the MCR.PGM bit from 0 to 1.
- 2. Ensure the block that contains the address to be programmed is unlocked.
 - Write the first address to be programmed with the program data. The Flash module latches address bits (22:3) at this time.
 - The Flash module latches data written as well.
 - This write is referred to as a program data interlock write. An interlock write may be as large as 64 bits, and as small as 32 bits (depending on the CPU bus).
- 3. If more than 1 word is to be programmed, write the additional address in the Double Word with data to be programmed. This is referred to as a program data write.
 - The Flash module ignores address bits (22:3) for program data writes.
 - The eventual unwritten data word default to 0xFFFFFFF.
- 4. Write logic 1 to the MCR.EHV bit to start the internal program sequence or skip to step 9 to terminate.
- 5. Wait until the MCR.DONE bit goes high.

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- Confirm MCR.PEG = 1.
- 7. Write logic 0 to the MCR.EHV bit.
- 8. If more addresses are to be programmed, return to step 2.
- 9. Write logic 0 to the MCR.PGM bit to terminate the program operation.

Program may be initiated with the 0 to 1 transition of the MCR.PGM bit or by clearing the MCR.EHV bit at the end of a previous program.

The first write after a program is initiated determines the page address to be programmed.

This first write is referred to as an interlock write. The interlock write determines if the shadow, test or normal array space will be programmed by causing MCR.PEAS to be set/cleared.

An interlock write must be performed before setting MCR.EHV. The user may terminate a program sequence by clearing MCR.PGM prior to setting MCR.EHV.

After the interlock write, additional writes only affect the data to be programmed at the word location determined by address bit 2. Unwritten locations default to a data value of 0xFFFFFFF. If multiple writes are done to the same location the data for the last write is used in programming.

While MCR.DONE is low and MCR.EHV is high, the user may clear EHV, resulting in a program abort.

A Program abort forces the module to step 8 of the program sequence.

An aborted program will result in MCR.PEG being set low, indicating a failed operation.

MCR.DONE must be checked to know when the aborting command has completed.

The data space being operated on before the abort will contain indeterminate data. This may be recovered by repeating the same program instruction or executing an erase of the affected blocks.

Example 1:

Double word program of data 0x55AA55AA at address 0x00AAA8 and data 0xAA55AA55 at address 0x00AAAC

```
MCR = 0x00000010; /* Set PGM in MCR: Select Operation */
  (0x00AAA8) = 0x55AA55AA; /* Latch Address and 32 LSB data */
  (0x00AAAC) = 0xAA55AA55; /* Latch 32 MSB data */
  MCR = 0x00000011; /* Set EHV in MCR: Operation Start */
  do /* Loop to wait for DONE=1 */
  { tmp = MCR; /* Read MCR */
  } while ( !(tmp & 0x00000400) );
  status = MCR & 0x00000200; /* Check PEG flag */
  MCR = 0x000000010; /* Reset EHV in MCR: Operation End */
  MCR = 0x000000000; /* Reset PGM in MCR: Deselect Operation */
```

2.2 Sector erase

Erase changes the value stored in all bits of the selected block(s) to logic 1.

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An erase sequence operates on any combination of blocks (sectors) in the low, mid or high address space, or the shadow block (if available). The test block cannot be erased.

The erase sequence is fully automated within the Flash. The user only needs to select the blocks to be erased and initiate the erase sequence.

Locked/disabled blocks cannot be erased.

If multiple blocks are selected for erase during an erase sequence, no specific operation order must be assumed.

The erase operation consists of the following sequence of events:

- 1. Change the value in the MCR.ERS bit from 0 to 1.
- Select the block(s) to be erased by writing '1's to the appropriate register(s) in LMS or HBS registers. If the shadow block is to be erased, this step may be skipped, and LMS and HBS are ignored.

Note that Lock and Select are independent. If a block is selected and locked, no erase will occur.

- 3. Write to any address in Flash. This is referred to as an erase interlock write.
- 4. Write a logic 1 to the MCR.EHV bit to start the internal erase sequence or skip to step 9 to terminate.
- 5. Wait until the MCR.DONE bit goes high.
- Confirm MCR.PEG = 1.
- 7. Write a logic 0 to the MCR.EHV bit.
- 8. If more blocks are to be erased, return to step 2.
- 9. Write a logic 0 to the MCR.ERS bit to terminate the erase operation.

After setting MCR.ERS, one write, referred to as an interlock write, must be performed before MCR.EHV can be set to '1'. Data words written during erase sequence interlock writes are ignored.

The user may terminate the erase sequence by clearing ERS before setting EHV.

An erase operation may be aborted by clearing MCR.EHV assuming MCR.DONE is low, MCR.EHV is high and MCR.ESUS is low.

An erase abort forces the module to step 8 of the erase sequence.

An aborted erase will result in MCR.PEG being set low, indicating a failed operation.

MCR.DONE must be checked to know when the aborting command has completed.

The block(s) being operated on before the abort contain indeterminate data. This may be recovered by executing an erase on the affected blocks.

The user may not abort an erase sequence while in erase suspend.

Example 2

Erase of sectors B0F1 and B0F2

```
MCR = 0 \times 000000004; /* Set ERS in MCR: Select Operation */
LMS = 0 \times 000000006; /* Set LSL2-1 in LMS: Select Sectors to erase */
(0 \times 0000000) = 0 \times FFFFFFFFF; /* Latch a Flash Address with any data */
MCR = 0 \times 000000005; /* Set EHV in MCR: Operation Start */
do /* Loop to wait for DONE=1 */
```



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3 Operation modes

To program the Flash it is possible use different strategy:

 Using the JTAG/NEXUS to access directly any addressable space so it is possible programming the Flash configuration registers and access directly the Flash areas to write.

 Download a code in RAM using the BAM features of the device. In that case through a serial communication link as UART or CAN, it is possible download a loader in RAM that will be executed after the BAM code and that will program the Flash.

In the second case the Loader code can access directly the Flash configuration registers or can use the Flash driver provided by ST.

In the following chapter it will be described the use of the Software drivers that by calls to specific functions allow programming the Flash without directly using the Flash configuration register.



4 Using the Flash library

The Standard Software Driver (SSD) is a set of API's that enables user application to operate on the Flash module embedded on a microcontroller. The C90LC SSD contains a set of functions to program/erase C90LC Flash modules on STMicroelectronics SPC56xx and RPC56xx microcontrollers.

The C90LC Standard Software Driver (SSD) provides the following API's:

- FlashInit
- FlashErase
- BlankCheck
- FlashProgram
- ProgramVerify
- CheckSum
- FlashSuspend
- FlashResume
- GetLock
- SetLock
- FlashArrayIntegrityCheck
- FlashECCLogicCheck
- FactoryMarginReadCheck

The C90LC SSD provides the following features:

- Two sets of driver binaries using 16-bit and 32-bit instruction set built on Power Architecture technology.
- Three sets of driver binaries built with three different tool chains.
- Drivers released in binary c-array format to provide compiler-independent support for non-debug-mode embedded applications.
- Drivers released in s-record format to provide compiler-independent support for debugmode/JTAG programming tools.
- Each driver function is independent of each other so the end user can choose the function subset to meet their particular needs.
- Support page-wise programming for fast programming.
- Position-independent and ROM-able
- Concurrency support via callback

4.1 Performing the programming

In order to use the Flash drivers to program the Flash, it is necessary execute the following steps:

- 1. Initializes the Flash library by calling FlashInit.
- 2. Remove the default lock of the Flash sector that you want program.
- Run the Program command of the API by calling pFlashProgram().

4.1.1 Sample code

```
void DoFlashProgram (rppaddress StartAddress, rppaddress EndAddress, const
unsigned char *buffer)
  SSD CONFIG ssdConfig = {
     C90FL_REG_BASE,
                            /* C90FL control register base */
     MAIN ARRAY BASE,
                            /* base of main array */
                            /* size of main array */
     Ο,
     SHADOW_ROW_BASE,
                            /* base of shadow row */
     SHADOW ROW SIZE,
                            /* size of shadow row */
                             /* block number in low address space */
     Ο,
                             /* block number in middle address space */
     Ο,
                             /* block number in high address space */
                            /* page size */
     C90FL PAGE SIZE,
     FALSE
                            /* debug mode selection */
  };
  UINT32lowEnabledBlocks = ;
  UINT32midEnabledBlocks = ;
  UINT32highEnabledBlocks = ;
  UINT8 addrSeq = ;
  MISR misrValue = ;
  UINT32rc
                    = 0;
  /* Initializes the FLASH */
  returnCode = pFlashInit( &ssdConfig );
  if( C90FL OK != returnCode )
     ErrorTrap(returnCode);
/*===== Unlock all blocks in low address space ======*/
    returnCode = pGetLock( &ssdConfig, LOCK LOW PRIMARY, &blkLockEnabled,
&blkLockState );
   if ( C90FL OK != returnCode )
    {
       ErrorTrap(returnCode);
    }
   returnCode = pSetLock( &ssdConfig, LOCK LOW PRIMARY, (blkLockState &
0xffffffc0), FLASH_LMLR_PASSWORD);
   if ( C90FL OK != returnCode )
        ErrorTrap(returnCode);
    }
```

```
returnCode = pGetLock( &ssdConfiq, LOCK LOW SECONDARY, &blkLockEnabled,
&blkLockState );
   if ( C90FL OK != returnCode )
       ErrorTrap(returnCode);
    }
   returnCode = pSetLock( &ssdConfig, LOCK_LOW_SECONDARY, (blkLockState &
0xFFFFFFC0), FLASH SLMLR PASSWORD);
   if ( C90FL OK != returnCode )
       ErrorTrap(returnCode);
    /*===== Unlock all blocks in mid address space =====*/
   returnCode = pGetLock( &ssdConfig, LOCK MID PRIMARY, &blkLockEnabled,
&blkLockState );
   if ( C90FL_OK != returnCode )
       ErrorTrap(returnCode);
    }
   returnCode = pSetLock( &ssdConfig, LOCK_MID_PRIMARY, (blkLockState &
0xfffffffc), FLASH_LMLR_PASSWORD);
   if ( C90FL OK != returnCode )
    {
       ErrorTrap(returnCode);
    }
     returnCode = pGetLock( &ssdConfig, LOCK MID SECONDARY,
&blkLockEnabled, &blkLockState );
   if ( C90FL OK != returnCode )
       ErrorTrap(returnCode);
    }
   returnCode = pSetLock( &ssdConfig, LOCK_MID_SECONDARY, (blkLockState &
0xfffffffc), FLASH_SLMLR_PASSWORD);
   if ( C90FL OK != returnCode )
       ErrorTrap(returnCode);
    }
    /*===== Unlock all blocks in high address space ======*/
   returnCode = pGetLock( &ssdConfig, LOCK HIGH, &blkLockEnabled,
&blkLockState );
```

```
if ( C90FL_OK != returnCode )
    {
        ErrorTrap(returnCode);
    }
    returnCode = pSetLock( &ssdConfig, LOCK_HIGH, (blkLockState &
0xfffffffc), FLASH_HLR_PASSWORD);
    if ( C90FL_OK != returnCode )
        ErrorTrap(returnCode);
    }
  /* Performs programming */
   returnCode = pFlashProgram( &ssdConfig, (UINT32)StartAddress,
((UINT32)EndAddress - (UINT32)StartAddress)+(UINT32)1, (UINT32)buffer,
pfnCallback);
  if( C90FL OK != returnCode ) {
     ErrorTrap(returnCode);
  /* All done */
```

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5 Library reference

For all details, please consider the User Manual of the software library (see *Appendix A: Document references*). Just for example, only the FlashInit() and FlashProgramming() function descriptions are reported.

5.1 FlashInit()

Description: This function reads the Flash configuration information from the Flash control

registers and initialize parameters in SSD configuration structure. 'FlashInit()' must be

called prior to any other Flash operations.

Definition: UINT32 FlashInit (PSSD CONFIG pSSDConfig);

Arguments:

Table 1. Arguments for FlashInit()

Argument	Description	Range
pSSDConfig	Pointer to the SSD Configuration Structure	The values in this structure are chip-dependent. Please refer to Section 2.3 for more details.

Returns:

Table 2. Return values for FlashInit()

Туре	Description	Possible values
UINT32	Indicates either success or failure type. It is a bit mapped return code so that more than one condition can be returned with a single return code. Each bit in the returned value, except for C90FL_OK, indicates a kind of current status of C90FL module	C90FL_OK C90FL_INFO_EER C90FL_INFO_RWE

Troubleshooting:

Table 3. Troubleshooting for FlashInit

Error codes	Possible causes	Solution	
C90FL_INFO_EER	An ECC Error occurred during a previous read	Clear FLASH_MCR-EER bit	
C90FL_INFO_RWE	A Read While Write Error occurred during a previous read	Clear the FLASH_MCR-RWE bit	

Comments:

'FlashInit()' will check the C90FL_MCR_RWE and C90FL_MCR_EER bit, but does not clear them when any of them is set. If RWE bit is set, Flash program/erase operations can still be performed.

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5.2 FlashProgram()

Description: This function will program the specified Flash areas with the provided source data.

Input arguments together with relevant Flash module status will be checked, and

relevant error code will be returned if there is any error.

Definition: UINT32 FlashProgram (PSSD CONFIG pSSDConfig,

UINT32 dest, UINT32 size, UINT32 source,

void (*CallBack)(void));

Arguments:

Table 4. Arguments for FlashProgram()

Argument	Description	Range
pSSDConfig	Pointer to the SSD Configuration Structure.	The values in this structure are chip-dependent.
Dest	Destination address to be programmed in Flash memory.	Any accessible address aligned on double word boundary in main array or shadow row.
Size	Size, in bytes, of the Flash region to be programmed.	If size = 0, C90FL_OK will be returned. It should be multiple of 8 and its combination with dest should fall in either main array or shadow row.
source	Source program buffer address.	This address must reside on word boundary.
CallBack	Address of void call back function pointer.	Any addressable void function address. To disable it use NULL_CALLBACK macro.

Returns:

Table 5. Return values for FlashProgram()

Text	Description	Possible values
UINT32	Successful completion or error value.	C90FL_OK C90FL_ERROR_BUSY C90FL_ERROR_ALIGNMENT C90FL_ERROR_RANGE C90FL_ERROR_PGOOD

AN4194 Library reference

Troubleshooting:

Table 6. Troubleshooting for FlashProgram()

Returned Error Bits	Description	Solution
C90FL_ERROR_BUSY	New program operation cannot be performed because the Flash module is busy with some operation and cannot meet the condition for starting a program operation.	Wait until the current operations finish. Conditions that program cannot start are: 1. program in progress (MCR-PGM high); 2. program not in progress (MCR-PGM low), but: a). erase in progress but not suspended; b). erase on main array is suspended but program is targeted to shadow row; c). erase on shadow row is suspended.
C90FL_ERROR_ALIGNMENT	This error indicates that dest/size/source isn't properly aligned	Check if <i>dest</i> and <i>size</i> are aligned on double word (64-bit) boundary. Check if source is aligned on word boundary.
C90FL_ERROR_RANGE	The area specified by dest and size is out of the valid C90LC address range.	Check <i>dest</i> and <i>dest+size</i> . Both should fall in the same C90LC address ranges, i.e. both in main array or both in shadow row
C90FL_ERROR_PGOOD	Program operation failed because this operation cannot pass PEG check.	Repeat the program operation. Check if the C90LC is invalid or high voltage applied to C90LC is unsuitable.

Comments:

If the selected main array blocks or the shadow row is locked for programming, those blocks or the shadow row will not be programmed, and 'FlashProgram()' will still return C90FL_OK. User needs to verify the programmed data with 'ProgramVerify()' function.

It is impossible to program any Flash block or shadow row when a program or erase operation is already in progress on C90LC module. 'FlashProgram()' will return C90FL_ERROR_BUSY when doing so. However, user can use the 'FlashSuspend()' function to suspend an on-going erase operation on one block to perform a program operation on another block. An exception is that once the user has begun an erase operation on the shadow row, it may not be suspended to program the main array and vice-versa.

It is unsafe to read the data from the Flash partitions having one or more blocks being programmed when *'FlashProgram()'* is running. Otherwise, it will cause a Read-While-Write error.

Assumptions:

It assumes that the Flash block is initialized using a 'FlashInit()' API.

Document references AN4194

Appendix A Document references

 Standard software driver for C90LC Flash in SPC560xx, SPC56APxx and SPC563M64xx (UM1584, Doc ID 023871)

- 2. SPC560D30L1, SPC560D30L3, SPC560D40L1, SPC560D40L3 32-bit MCU family built on the embedded Power Architecture® (RM0045, DocID 16886)
- 3. SPC560B4x, SPC560B50, SPC560C4x, SPC560C50 32-bit MCU family built on the embedded Power Architecture[®] (RM0017, DocID 14629)
- 4. Support microcontrollers SPC560B54x, SPC560B60x and SPC560B64x (RM0037, DocID 15700)
- 5. SPC560P34/SPC560P40 32-bit MCU family built on the embedded Power Architecture® (RM0046, Doc ID 16912)
- 6. 32-bit MCU family built on the Power Architecture® embedded category for automotive chassis and safety electronics applications (RM0022, DocID 14891)
- 7. 32-bit MCU family built on the Power Architecture® embedded category for automotive chassis and safety electronics applications (RM0083, DocID 018714)
- 8. SPC563M64xx 32-bit Power Architecture® based MCU with up to 1.5 Mbyte Flash and 111 Kbyte RAM memories (RM0015, DocID 14499)

AN4194 Revision history

Revision history

Table 7. Document revision history

Date	Revision	Changes	
12-Nov-2012	1	Initial release.	
13-Sep-2013 2		Updated disclaimer.	
19-Oct-2015 3 Robust root part numbers added.		Robust root part numbers added.	

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